AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 7, line 17 as shown below.

At time t_2, as shown in Fig. 4C, transfer control signal T_X is set to a high state, sufficiently high for voltage V_C of channel region 11 to be greater than Vdd. The voltage of read region 7 increases to reach a voltage V_0 due to the coupling between transistor M_4 and read region 7. This enables increasing the electric field favoring the charge transfer from photodiode D to read node S. The charges stored at the level of photodiode D flow to read region 7 and [[raise]] diminish the voltage of this region to value V_1. In the case where charge Q is relatively low, voltage V_1 may be greater than Vdd and greater than V_C. Hatched region Q' delimited by voltages V_0 and V_1 shows the charges stored at the level of read region 7.

Please replace the paragraph beginning on page 8, line 2 as shown below.

At time t_4, as shown in Fig. 4E, reset control signal RST is set to the low state. The voltage of channel region 12 of transistor M_1 thus increases to enable flowing of charges [[Q"]] Q' stored at the level of read region 7 to supply region 8. The voltages of regions 7, 12, and 8 thus stabilize at the level of supply voltage Vdd.